

Amendments to the Specification:

Please replace the paragraph bridging pages 39 and 40 with the following amended paragraph:

Next, as shown in FIG. 15D, the island-like semiconductor film 1706 to be a p-channel TFT is covered with a resist 1713 and the island-like semiconductor layers 1705 and 1707 are doped with an impurity element imparting n-type conductivity (typically P (phosphorus) or [[Ar]] As (arsenic)) at low concentration by using the gate electrodes 1709 and 1711 as a mask. In this doping step, doping is conducted through the gate insulating film 1708, and a pair of low-concentration impurity regions 1716 and 1717 is formed in the island-like semiconductor layers 1716 and 1717. This doping step may be conducted without covering the island-like semiconductor film 1706 to be the p-channel TFT with the resist.